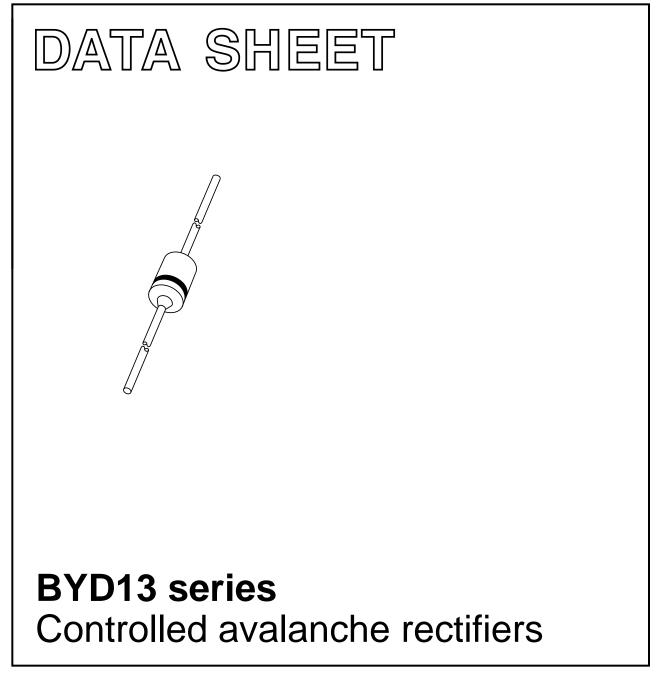
DISCRETE SEMICONDUCTORS



Product specification Supersedes data of April 1992 File under Discrete Semiconductors, SC01 1996 May 24



Philips Semiconductors

FEATURES

- · Glass passivated
- High maximum operating temperature
- Low leakage current
- · Excellent stability
- Guaranteed avalanche energy absorption capability
- Available in ammo-pack.

DESCRIPTION

Cavity free cylindrical glass package through Implotec^{TM(1)} technology.

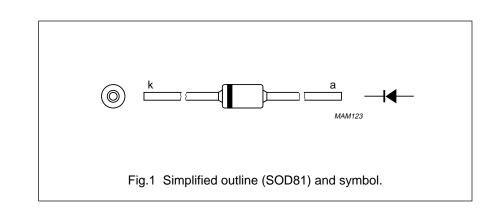
This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

(1) Implotec is a trademark of Philips.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{RRM}	repetitive peak reverse voltage				
	BYD13D		_	200	V
	BYD13G		_	400	V
	BYD13J		_	600	V
	BYD13K		_	800	V
	BYD13M		_	1000	V
V _{RWM}	crest working reverse voltage				
	BYD13D		_	200	V
	BYD13G		_	400	V
	BYD13J		_	600	V
	BYD13K		_	800	V
	BYD13M		_	1000	V
V _R	continuous reverse voltage				
	BYD13D		_	200	V
	BYD13G		_	400	V
	BYD13J		_	600	V
	BYD13K		_	800	V
	BYD13M		_	1000	V



MARKING

TYPE NUMBER	MARKING CODE
BYD13D	13D PH
BYD13G	13G PH
BYD13J	13J PH
BYD13K	13K PH
BYD13M	13M PH

BYD13 series

BYD13 series

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{F(AV)}	average forward current	T_{tp} = 55 °C; lead length = 10 mm; averaged over any 20 ms period; see Figs 2 and 4	_	1.40	A
		T_{amb} = 65 °C; PCB mounting (see Fig.9); averaged over any 20 ms period; see Figs 3 and 4	_	0.75	A
I _{FSM}	non-repetitive peak forward current	t = 10 ms half sinewave; $T_j = T_{j max}$ prior to surge; $V_R = V_{RRMmax}$	_	20	A
E _{RSM}	non-repetitive peak reverse avalanche energy	L = 120 mH; $T_j = T_{j max}$ prior to surge; inductive load switched off	_	7	mJ
T _{stg}	storage temperature		-65	+175	°C
Tj	junction temperature	see Fig.5	-65	+175	°C

ELECTRICAL CHARACTERISTICS

 $T_j = 25 \ ^{\circ}C$; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _F	forward voltage	$I_F = 1 \text{ A}; T_j = T_{j \text{ max}}$ see Fig.6	_	-	0.93	V
		I _F = 1 A; see Fig.6	—	—	1.05	V
V _{(BR)R}	reverse avalanche breakdown voltage	I _R = 0.1 mA				
	BYD13D		225	-	-	V
	BYD13G		450	_	_	V
	BYD13J		650	-	-	V
	BYD13K		900	-	-	V
	BYD13M		1100	-	-	V
I _R	reverse current	$V_R = V_{RRMmax}$; see Fig.7	_	-	1	μΑ
		$V_R = V_{RRMmax}$; $T_j = 165 \text{ °C}$; see Fig.7	_	-	100	μΑ
t _{rr}	reverse recovery time	when switched from $I_F = 0.5$ A to $I_R = 1$ A; measured at $I_R = 0.25$ A; see Fig.10	_	3	_	μs
C _d	diode capacitance	$V_R = 0 V$; f = 1 MHz; see Fig.8	_	21	_	pF

THERMAL CHARACTERISTICS

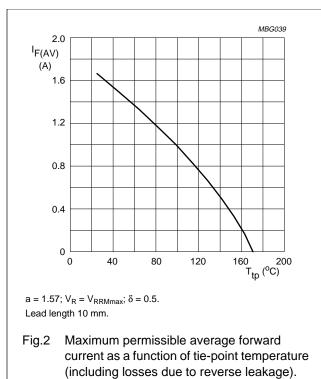
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-tp}	thermal resistance from junction to tie-point	lead length = 10 mm	60	K/W
R _{th j-a}	thermal resistance from junction to ambient	note 1	120	K/W

Note

1. Device mounted on epoxy-glass printed-circuit board, 1.5 mm thick; thickness of copper ≥40 μm, see Fig.9. For more information please refer to the *"General Part of Handbook SC01"*.

BYD13 series

GRAPHICAL DATA



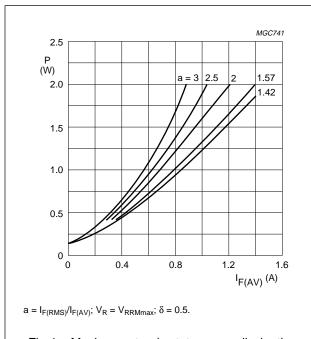
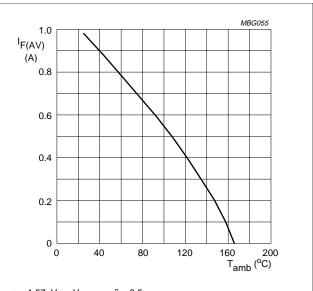
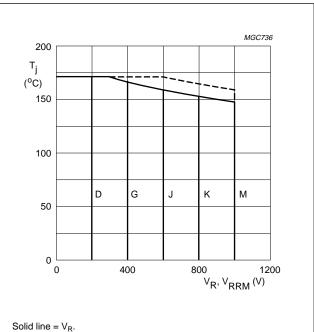


Fig.4 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.



a = 1.57; $V_R = V_{RRMmax}$; $\delta = 0.5$. Device mounted as shown in Fig.9.

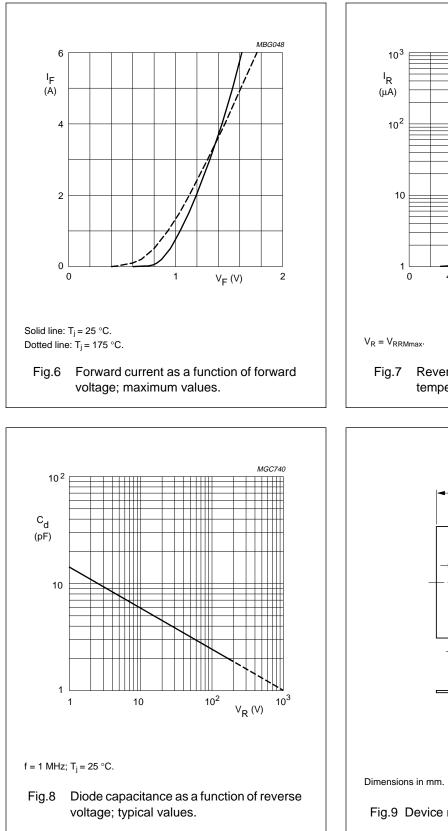
Fig.3 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).



Dotted line = V_{RRM} ; $\delta = 0.5$.

Fig.5 Maximum permissible junction temperature as a function of reverse voltage.

BYD13 series



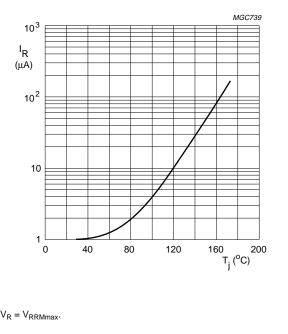


Fig.7 Reverse current as a function of junction temperature; maximum values.

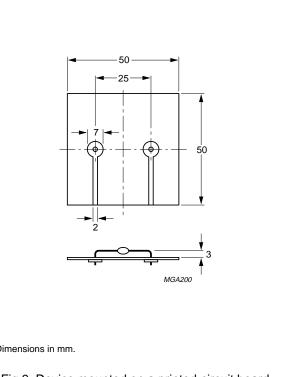
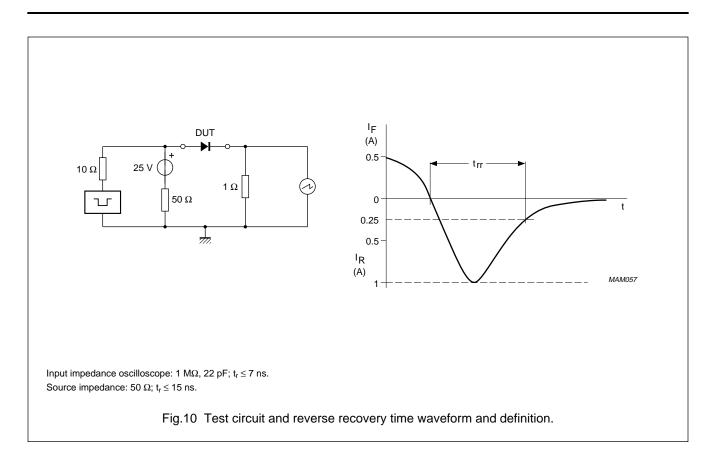


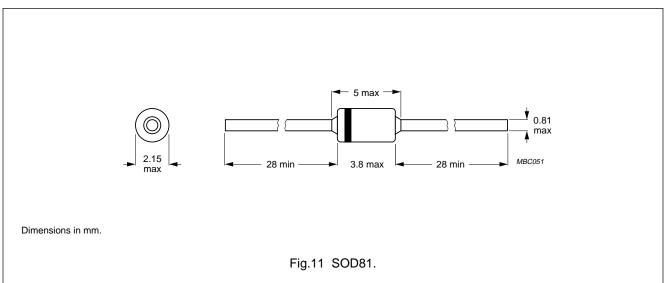
Fig.9 Device mounted on a printed-circuit board.

BYD13 series



BYD13 series

PACKAGE OUTLINE



DEFINITIONS

et or goal specifications for product development. minary data; supplementary data may be published later. product specifications.
product specifications.
Aximum Rating System (IEC 134). Stress above one or to the device. These are stress ratings only and operation be given in the Characteristics sections of the specification ods may affect device reliability.
bes not form part of the specification.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.